

**Amendments to the Claims**

Please amend the claims as follows.

1-86. (canceled)

87. (currently amended) A method of fabricating a semiconductor device, comprising:  
mounting a second surface of a die on a support substrate, the die having a first surface  
with at least one standoff attached thereto, the standoff being exposed and formed on only part of  
the first surface of the die with a portion of said first die surface exposed.

88. (original) The method of Claim 87, wherein the die is flip chip mounted on the support  
substrate.

89. (currently amended) A method of fabricating a semiconductor device, comprising:  
forming a standoff on a first surface of a die such that the standoff is exposed and formed  
on only part of the first surface of the die with a portion of said first die surface exposed; and  
mounting the second surface of the die on a first surface of a support substrate.

90. (previously presented) The method of Claim 89, wherein forming the standoff comprises  
dispensing a material on the first surface of the die by a method selected from the group  
consisting of screen printing, stenciling, coating, masking, stamping, heat stamping, spray  
coating, and direct spreading.

91. (withdrawn) The method of Claim 89, wherein forming the standoff comprises a process  
selected from the group consisting of electroplating and anodizing.

92. (previously presented) The method of Claim 89, wherein forming the standoff comprises  
dispensing a flowable material onto the die and allowing the flowable material to solidify.

93. (original) The method of Claim 92, wherein the flowable material is dispensed using a liquid capillary.
94. (original) The method of Claim 92, wherein the flowable material is a curable thermoset polymeric material.
95. (original) The method of Claim 94, wherein the polymeric material is a novolac epoxy resin.
96. (withdrawn) The method of Claim 89, wherein the standoff comprises a prefabricated object, and forming the standoff comprises affixing the object to the surface of the die.
97. (withdrawn) The method of Claim 96, wherein the object is affixed using an adhesive material.
98. (withdrawn) The method of Claim 97, wherein the adhesive material comprises an adhesive paste.
99. (withdrawn) The method of Claim 97, wherein the adhesive material comprises a double-sided adhesive tape.
100. (withdrawn) The method of Claim 97, wherein the standoff comprises an adhesive-backed decal.
101. (withdrawn) The method of Claim 96, wherein the standoff comprises a thermally conductive material.
102. (withdrawn) The method of Claim 101, wherein the conductive material is selected from the group consisting of copper, aluminum, gold and silver.

103. (original) The method of Claim 102, wherein the standoff comprises a copper foil.
104. (previously presented) The method of Claim 89, wherein the standoff comprises a plastic material, and forming the standoff comprises a process selected from the group consisting of injection molding, extrusion, blow molding, compression molding, transfer molding, and thermoforming.
105. (withdrawn) The method of Claim 89, wherein forming the standoff comprises an electroplating or anodizing process.
106. (withdrawn) The method or Claim 105, wherein the standoff comprises a thermally conductive material.
107. (withdrawn) The method or Claim 106, wherein the conductive material is selected from the group consisting of silver, copper, aluminum, gold and nickel.
108. (previously presented) The method of Claim 89, wherein the standoff is in the form of an enclosure, and the method further comprises applying a heat sink material on the surface of the die within the standoff enclosure.
109. (original) The method of Claim 108, wherein the heat sink material comprises copper or aluminum.
110. (original) The method of Claim 109, comprising adhering a layer of copper foil to the surface of the die to form the heat sink.
111. (original) The method of Claim 89, wherein the die is flip chip mounted on the support substrate.

112. (withdrawn) The method of Claim 89, further comprising:  
mounting a second surface of a second die on a second surface of the support substrate,  
wherein at least one standoff is affixed to the first surface of the second die and exposed on said  
die.

113. (withdrawn - currently amended) A method of fabricating a semiconductor device,  
comprising:

forming a standoff on a first surface of each of a pair of dies, wherein the standoffs are  
exposed and formed on only part of said first surfaces of the dies with a portion of said first die  
surfaces exposed; and

mounting the dies on opposing sides of a support substrate, the second surface of each of  
the dies situated on the substrate.

114. (withdrawn - currently amended) A method of fabricating a semiconductor die package,  
comprising:

positioning a die/substrate unit within a molding chamber of a mold tooling, the  
die/substrate unit comprising a semiconductor die on a support substrate, the die having a first  
surface with one or more standoffs attached thereto, the standoffs having a height and on only  
part of the first surface of the die with a portion of said first die surface exposed, and a second  
surface situated on the support substrate; and the mold tooling comprising a pair of mold plates  
defining the molding chamber therebetween, the mold plates having an inner surface, wherein  
the standoffs are in contact with the inner surfaces of the mold plates; and

flowing a molding compound into the molding chamber to at least partially encapsulate  
the die/substrate unit, wherein the die/substrate unit is maintained in a centralized and  
substantially planar orientation within the molding chamber as the molding compound is flowed  
thereabout.

115. (withdrawn - currently amended) A method of fabricating a semiconductor die package, comprising:

positioning a die/substrate unit within a molding chamber between a pair of mold plates each having an inner surface, the die/substrate unit comprising a semiconductor die on a support substrate, the die having a first surface with one or more standoffs attached thereto, the standoffs having a height and situated on only part of the first surface of the die with a portion of said first die surface exposed, and a second surface situated on the support substrate, such that the standoffs are in contact with the inner surfaces of the mold plates; and

introducing a molding compound into the molding chamber, wherein the die/substrate unit is maintained in a centralized and substantially planar orientation within the molding chamber as the molding compound is flowed thereabout.

116. (withdrawn - currently amended) A method of fabricating a semiconductor die package, comprising:

positioning a die/substrate unit within a molding chamber between a pair of mold plates each having an inner surface, the die/substrate unit comprising a semiconductor die on a support substrate, the die having a first surface with one or more standoffs affixed thereto, the standoffs having a height and situated on only part of the first surface of the die with a portion of said first die surface exposed, and a second surface situated on the support substrate, such that the standoffs are in contact with the inner surfaces of the mold plates; and

introducing a molding compound into the molding chamber, wherein the die/substrate unit is maintained in a centralized and substantially planar orientation within the molding chamber as the molding compound is flowed thereabout.

117. (withdrawn - currently amended) A method of fabricating a semiconductor die package, comprising the steps of:

positioning a semiconductor device within a molding chamber between a pair of mold plates each having an inner surface, the semiconductor device comprising a pair of semiconductor dies situated on opposing sides of a support substrate, each die having a first surface with one or more standoffs affixed to a part of the first surface with a portion of said first

die surface exposed, and a second surface situated on the support substrate, such that the standoffs are in contact with the inner surfaces of the mold plates; and

introducing a molding compound into the molding chamber, wherein the support substrate of the semiconductor device is maintained in a centralized and substantially planar orientation within the molding chamber as the molding compound is flowed thereabout.

118. (withdrawn - currently amended) A method of fabricating a semiconductor die package, comprising:

positioning a semiconductor device within a molding chamber between a pair of mold plates each having an inner surface, the semiconductor device comprising a pair of semiconductor dies mounted on opposing sides of a support substrate, each die having a standoff attached to a portion of the surface of the each of the dies and exposed on said dies with a portion of said die surfaces exposed such that the standoffs are in contact with the inner surfaces of the mold plates; and

introducing a molding compound into the molding chamber, wherein the support substrate of the semiconductor device is maintained in a centralized and substantially planar orientation within the molding chamber as the molding compound is flowed thereabout.

119. (withdrawn - currently amended) A method of fabricating a semiconductor die package, comprising the steps of:

positioning a semiconductor device within a molding chamber between a pair of mold plates each having an inner surface, the semiconductor device comprising a pair of dies, each die having a standoff attached to a portion of a first surface of the dies with a portion of said first die surface exposed, the dies mounted on opposing sides of a support substrate with the standoff exposed such that the standoffs are in contact with the inner surfaces of the mold plates; and

introducing a molding compound into the molding chamber, wherein the support substrate of the semiconductor device is maintained in a centralized and substantially planar orientation within the molding chamber as the molding compound is flowed thereabout.

120. (withdrawn) A method of fabricating a semiconductor die package, comprising:  
positioning a semiconductor device within a molding chamber between a pair of mold plates defining a molding chamber therebetween, the semiconductor device comprising a pair of semiconductor dies situated on opposing sides of a support substrate, and each mold plate having an inner surface with a standoff situated thereon such that the standoffs are in contact with the first surfaces of the dies; and

introducing a molding compound into the molding chamber, wherein the support substrate of the semiconductor device is maintained in a centralized and substantially planar orientation within the molding chamber as the molding compound is flowed thereabout.

121. (withdrawn - currently amended) A method of fabricating a semiconductor dic package, comprising:

positioning a semiconductor device within a molding chamber between a pair of mold plates each having an inner surface, the semiconductor device comprising a pair of semiconductor dies mounted on opposing sides of a support substrate, each die having a standoff attached to a part of a first surface with a portion of said first die surface exposed and the second surface of each of the dies situated on the support substrate, such that the standoffs are in contact with the inner surfaces of the mold plates; and

introducing a molding compound into the molding chamber, wherein the support substrate of the semiconductor device is maintained in a centralized and substantially planar orientation within the molding chamber as the molding compound is flowed therewith.

122. (currently amended) A method of fabricating a semiconductor die, comprising:

forming at least one standoff on a surface of the semiconductor die, the standoff being exposed and formed on only part of said surface of the die with a portion of said die surface exposed.

123. (previously presented) The method of Claim 122, wherein forming the standoff comprises dispensing a material on the surface of the dic by a method selected from the group

consisting of screen printing, stenciling, coating, masking, stamping, heat stamping, spray coating, and direct spreading.

124. (withdrawn) The method of Claim 122, wherein forming the standoff comprises a process selected from the group consisting of electroplating and anodizing.

125. (previously presented) The method of Claim 122, wherein forming the standoff comprises dispensing a flowable material onto the die and allowing the flowable material to solidify.

126. (previously presented) The method of Claim 125, wherein dispensing the flowable material is by use of a liquid capillary.

127. (previously presented) The method of Claim 125, wherein the flowable material comprises a curable thermoset polymeric material.

128. (withdrawn) The method of Claim 122, wherein forming the standoff comprises mounting a prefabricated object to the surface of the die.

129. (withdrawn) The method of Claim 128, wherein the object is mounted using an adhesive paste, a double-sided adhesive tape, or a combination thereof.

130. (withdrawn) The method of Claim 128, wherein mounting the standoff comprises affixing an adhesive-backed object to the at least one surface of the die.

131. (withdrawn) The method of Claim 122, wherein the standoff comprises a thermally conductive material.

132. (withdrawn) The method of Claim 122, wherein the standoff comprises a conductive material selected from the group consisting of copper, aluminum, gold and silver.

133. (withdrawn) The method of Claim 132, wherein the standoff comprises a copper foil.

134. (previously presented) The method of Claim 122, wherein the standoff comprises a plastic material.

135. (previously presented) The method of Claim 122, further comprising forming ball contacts on a second surface of the die.

136. (previously presented) The method of Claim 122, further comprising mounting the die on a support substrate.

137. (currently amended) A method of fabricating a semiconductor die, comprising:  
forming at least one standoff on a surface of the die, the standoff being in the form of an enclosure; and  
forming a heat sink within the standoff enclosure wherein a portion of said die surface is exposed.

138. (previously presented) The method of Claim 137, wherein the heat sink comprises copper or aluminum.

139. (previously presented) The method of Claim 137, wherein forming the heat sink comprises adhering a layer of copper foil to the surface of the die within the standoff enclosure.

140. (currently amended) A method of fabricating a semiconductor device, comprising:  
affixing at least one standoff onto a first surface of the die, the standoff being exposed and affixed only on a part of the first surface of the die with a portion of said first die surface exposed; and  
mounting a second surface of the die on a first surface of a support substrate.

141. (previously presented) The method of Claim 140, wherein the support substrate comprises a flexible material.

142. (previously presented) The method of Claim 141, wherein the support substrate comprises a polyimide film.

143. (previously presented) The method of Claim 140, wherein the support substrate comprises a rigid material.

144. (previously presented) The method of Claim 143, wherein the rigid material is selected from the group consisting of a polymer material, ceramic material, metal clad fiber board, and metal leadframe.

145. (previously presented) The method of Claim 144, wherein the support substrate comprises a polymer material selected from the group consisting of bismaleimide triazine resin, epoxy resin, FR-4 laminate, and FR-5 laminate.

146. (previously presented) The method of Claim 140, further comprising forming external contacts on the second surface of the support substrate.

147. (previously presented) The method of Claim 146, further comprising mounting the external contacts on the support substrate onto a second support substrate.

148. (currently amended) A method of fabricating a semiconductor device, comprising:  
affixing at least one standoff onto a first surface of the die, the standoff being exposed  
and affixed only on a part of the first surface of the die with a portion of said first die surface  
exposed; and

mounting a second surface of the die on a first surface of a support substrate, the support  
substrate having contact pads on a second surface and an opening to expose bond pads on the  
second surface of the die; and

connecting the bond pads on the second surface of the die through the opening to the contact pads on the second surface of the support substrate.

149. (previously presented) The method of Claim 148, further comprising encapsulating at least the connection between the bond pads and the contact pads.

150. (previously presented) The method of Claim 148, further comprising forming external contacts on the second surface of the support substrate.

151. (currently amended) A method of fabricating a semiconductor device, comprising:  
affixing at least one standoff onto a surface of the die, the standoff being exposed on the die and affixed only on a part of said surface of the die with a portion of said first die surface exposed;

mounting an opposing surface of the die on a support substrate; and  
connecting bond pads on the die to contact pads on the support substrate.

152. (withdrawn) The method of Claim 92, wherein forming the standoff comprises dispensing the flowable material by a method selected from the group consisting of screen printing, stenciling, coating, masking, stamping, heat stamping, spray coating, and direct spreading.

153. (withdrawn) The method of Claim 122, wherein forming the standoff comprises dispensing the flowable material by a method selected from the group consisting of screen printing, stenciling, coating, masking, stamping, heat stamping, spray coating, and direct spreading.

154. (currently amended) A method of fabricating a die, comprising forming a standoff on a first portion of a surface of the die with a second portion of said die surface exposed, the standoff having a sufficient height and exposed on the die such that when the die is positioned in a mold

cavity between two mold plates, the at least one standoff contacts an inner surface of one of the mold plates.

155. (previously presented) A method of fabricating a die, comprising forming a plurality of standoffs on a surface of the die.

156. (previously presented) A method of fabricating a die, comprising forming a plurality of standoffs on a surface of the die, the standoffs being raised structures affixed to the surface of the die to maintain the surface of the die spaced apart from a mold plate during a die encapsulation process.

157. (previously presented) A method of fabricating a die, comprising forming a plurality of standoffs on a surface of the die, the standoffs being raised structures and exposed on the die to effectively contact an inner surface of a mold such that the surface of the die is spaced apart from the inner surface of the mold.